



TO-92L Plastic-Encapsulate Transistors

2SC1383

TRANSISTOR (NPN)

2SC1384**FEATURE**

Power dissipation

 P_{CM} : 1 W ($T_{amb}=25^{\circ}C$)

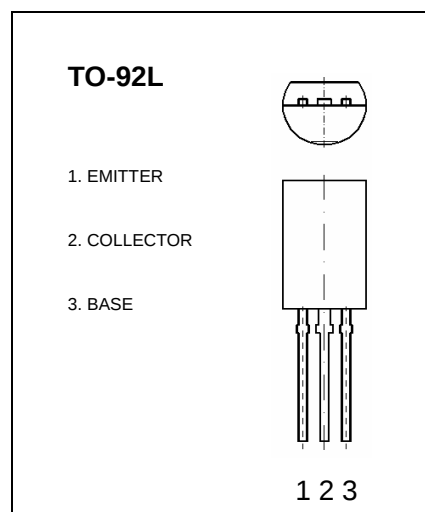
Collector current

 I_{CM} : 1 A

Collector-base voltage

 $V_{(BR)CBO}$: 2SC1383: 30 V
2SC1384: 50 V

Operating and storage junction temperature range

 T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$ **ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30 60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=2mA, I_B=0$	25 50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10V, I_C=500mA$	85	340	
	$h_{FE(2)}$	$V_{CE}=5V, I_C=1A$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$		0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500mA, I_B=50mA$		1.2	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA$	100		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R	S
Range	85-170	120-240	170-340